

## 800V 2.1Ω Super Junction Power MOSFET

### Description

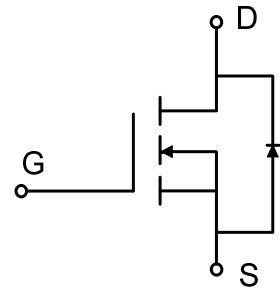
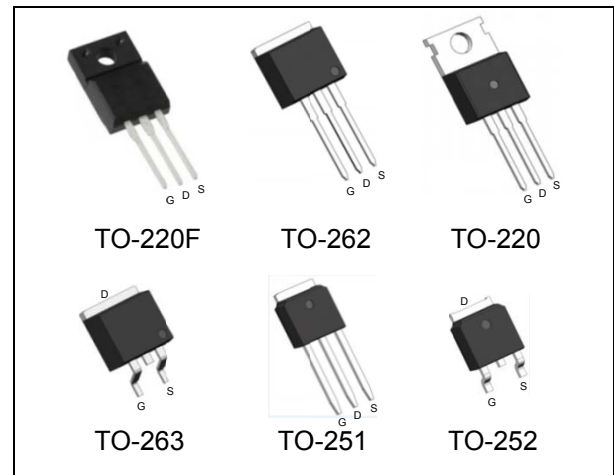
WMOS™ M3 is Wayon's 3<sup>rd</sup> generation 800V super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ M3 is suitable for applications which require superior power density and outstanding efficiency.

### Features

- $V_{DS} = 850V @ T_{j,max}$
- Typ.  $R_{DS(on)} = 2.1\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

### Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



### Absolute Maximum Ratings

Parameter	Symbol	WMN/WMM/WMO/WMP/WMK	WML	Unit
Drain-source voltage	$V_{DSS}$	800		V
Continuous drain current <sup>1)</sup> ( $T_C = 25^\circ C$ )	$I_D$	4		A
		2.2		A
Pulsed drain current <sup>2)</sup>	$I_{DM}$	11		A
Gate-source voltage	$V_{GS}$	$\pm 30$		V
Avalanche energy, single pulse <sup>3)</sup>	$E_{AS}$	15		mJ
Avalanche energy, repetitive <sup>2)</sup>	$E_{AR}$	0.07		mJ
Avalanche current, repetitive <sup>2)</sup>	$I_{AR}$	0.7		A
Power dissipation ( $T_C = 25^\circ C$ ) - Derate above $25^\circ C$	$P_D$	45	23	W
		0.36	0.18	W/ $^\circ C$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150		$^\circ C$
Continuous diode forward current	$I_S$	4		A
Diode pulse current	$I_{S,pulse}$	11		A

### Thermal Characteristics

Parameter	Symbol	WMN/WMM/WMO/WMP/WMK	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	2.4	5.4	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

**Electrical Characteristics**  $T_c = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS}=0\text{ V}, I_D=0.25\text{ mA}$	800	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{ mA}$	2.5	3.3	4.5	V
Drain cut-off current	$I_{DSS}$	$V_{DS}=800\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1	$\mu\text{A}$
Gate leakage current, forward	$I_{GSSF}$	$V_{GS}=30\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, reverse	$I_{GSSR}$	$V_{GS}=-30\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=1\text{ A}$ $T_j = 25^\circ\text{C}$	-	2.1	2.5	$\Omega$
<b>Dynamic characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS}= 50\text{ V}, V_{GS}= 0\text{ V},$	-	298	-	pF
Output capacitance	$C_{oss}$	$f = 1\text{ MHz}$	-	14	-	
Reverse transfer capacitance	$C_{rss}$		-	1.3	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 300\text{V}, I_D = 1\text{ A}$	-	21	-	ns
Rise time	$t_r$	$R_G = 25\Omega, V_{GS}=10\text{V}$	-	13	-	
Turn-off delay time	$t_{d(off)}$		-	40	-	
Fall time	$t_f$		-	18	-	
<b>Gate charge characteristics</b>						
Gate to source charge	$Q_{gs}$	$V_{DD}=480\text{ V}, I_D=1\text{ A},$	-	1.5	-	nC
Gate to drain charge	$Q_{gd}$	$V_{GS}=0\text{ to }10\text{ V}$	-	6.7	-	
Gate charge total	$Q_g$		-	10.5	-	
Gate plateau voltage	$V_{plateau}$		-	5.2	-	V
<b>Reverse diode characteristics</b>						
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=1\text{ A}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{ V}, I_F=1\text{ A},$	-	190	-	ns
Reverse recovery charge	$Q_{rr}$	$dI_F/dt=100\text{ A}/\mu\text{s}$	-	0.65	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	6	-	A

## Notes:

- Limited by  $T_{j\text{max}}$ . Maximum duty cycle  $D=0.5$ .
- Repetitive rating: pulse width limited by maximum junction temperature
- $I_{AS} = 0.7\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\Omega$ , starting  $T_j = 25^\circ\text{C}$

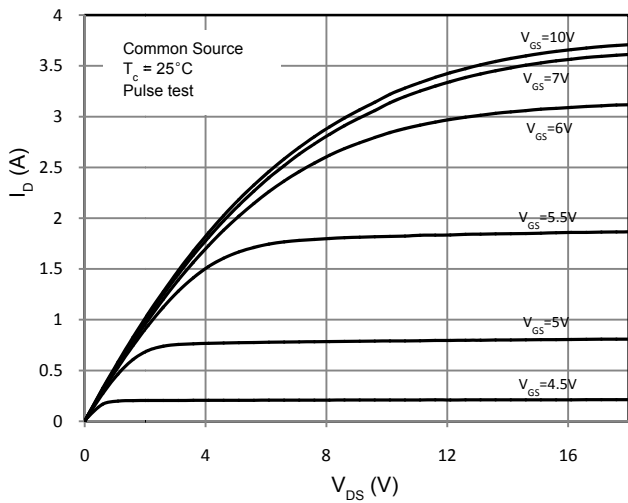


Figure 1. On-Region Characteristics

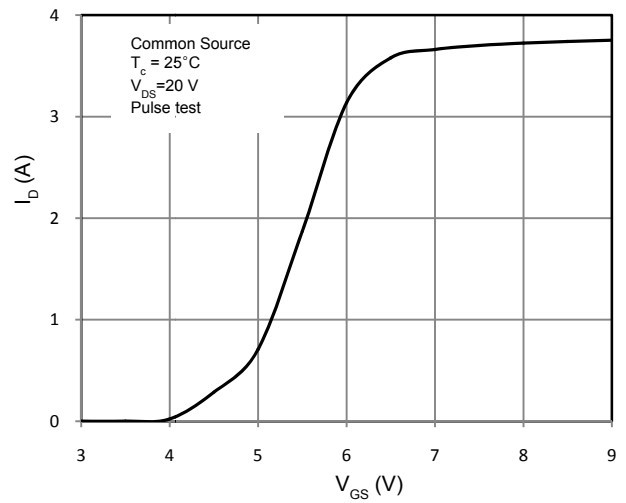


Figure 2. Transfer Characteristics

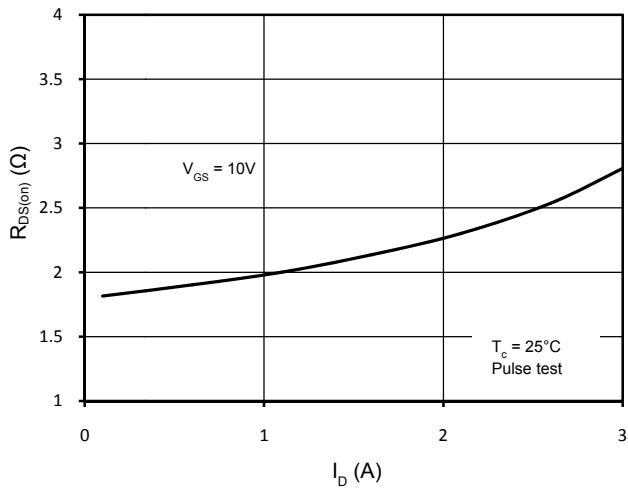


Figure 3. Static Drain-Source On Resistance

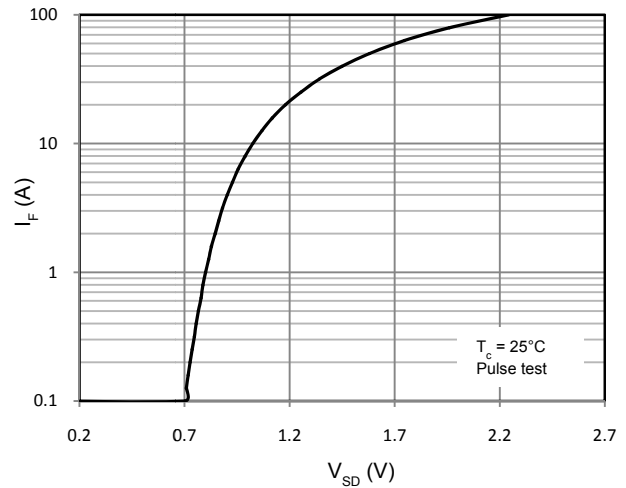


Figure 4. Body-Diode Forward Characteristics

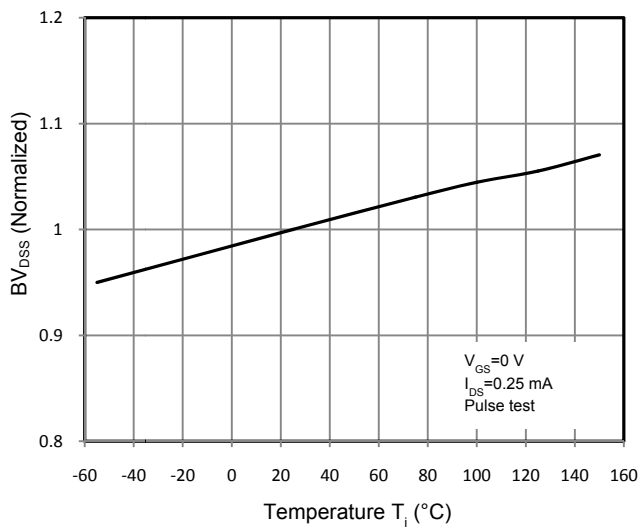


Figure 5. Normalized  $BV_{DS(sat)}$  vs. Temperature

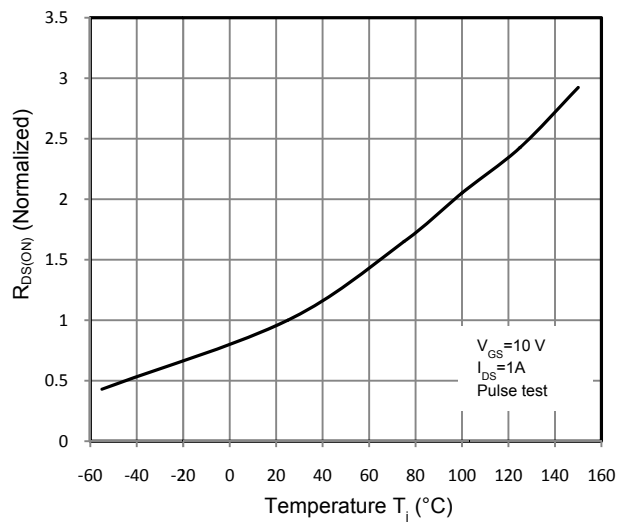


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature

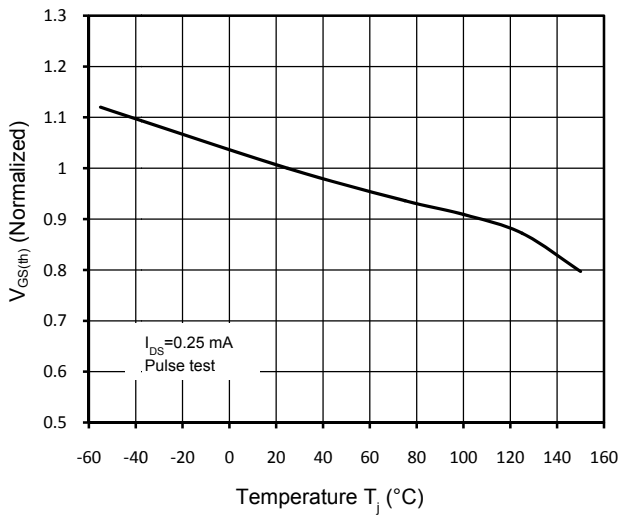


Figure 7. Threshold Voltage vs. Temperature

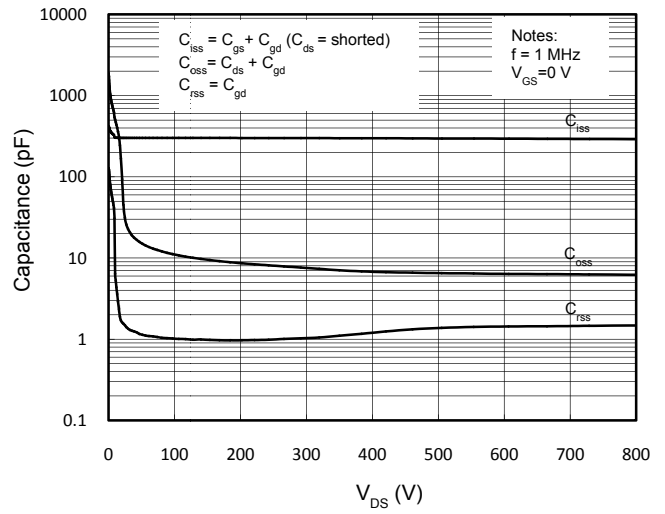


Figure 8. Capacitance Characteristics

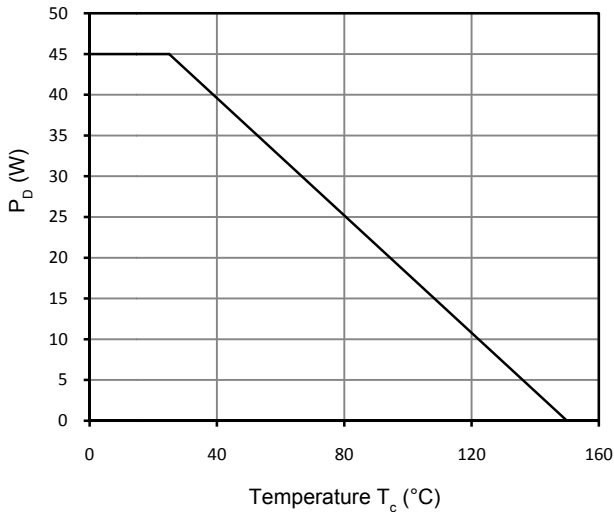


Figure 9. Power Dissipation

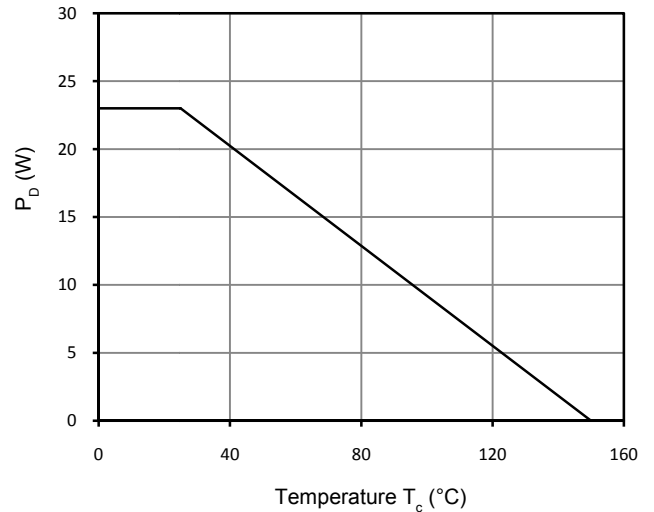


Figure 10. Power Dissipation (TO-220F)

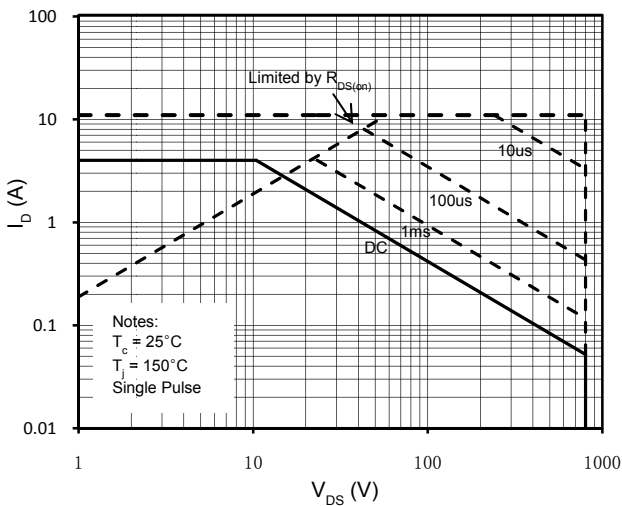


Figure 11. Maximum Safe Operating Area

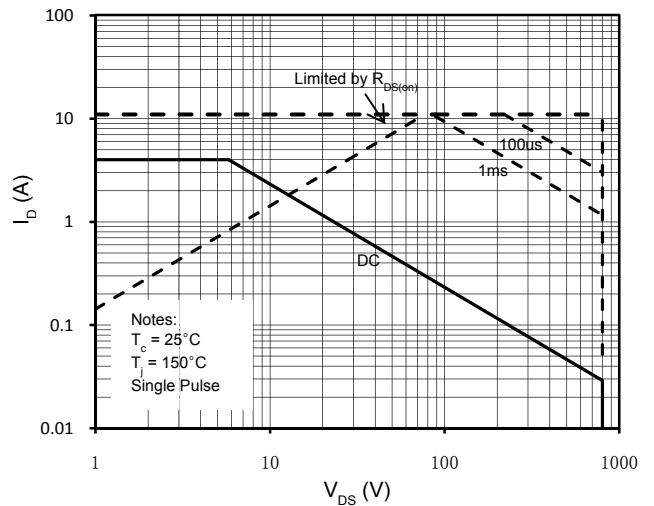


Figure 12. Maximum Safe Operating Area (TO-220F)

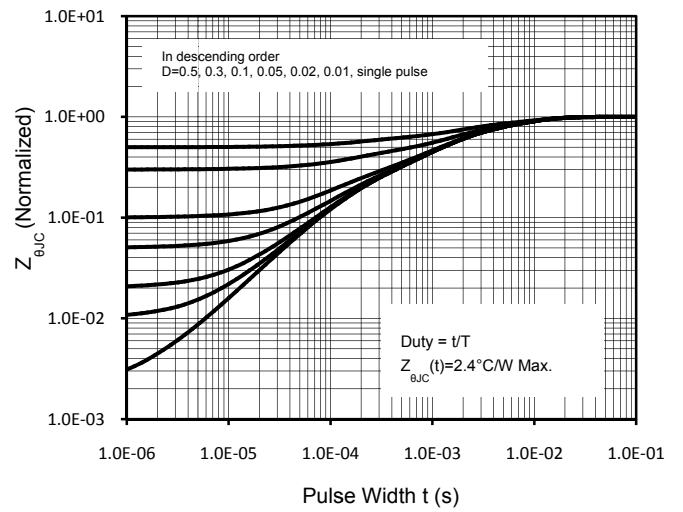
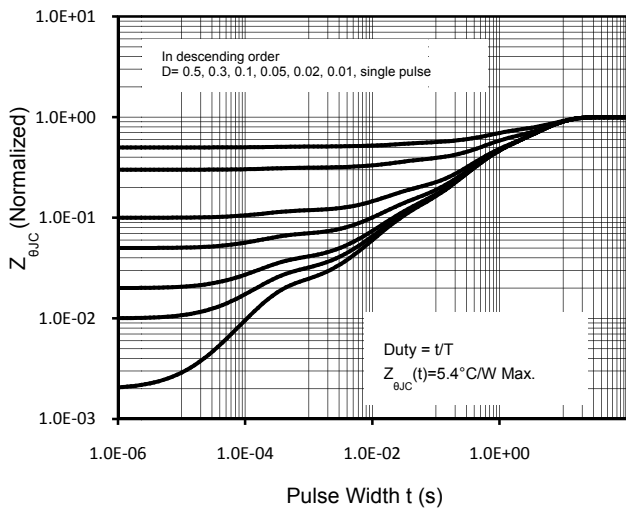


Figure 13. Transient Thermal Response Curve (TO-220F) Figure 14. Transient Thermal Response Curve

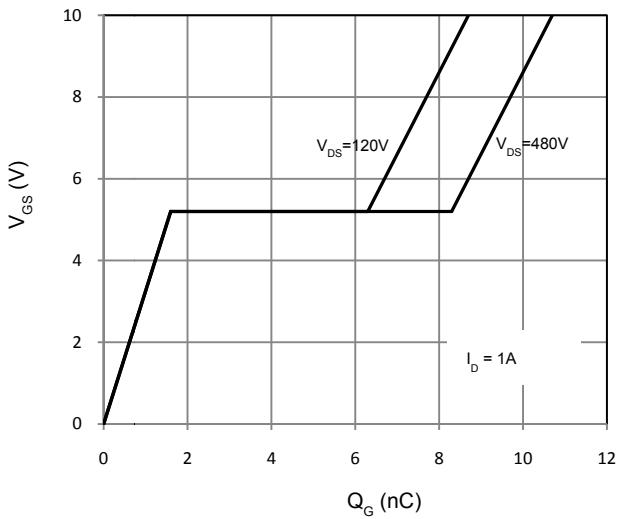


Figure 15. Gate Charge Characteristics

**Gate Charge Test Circuit & Waveform**



**Switching Test Circuit & Waveforms**

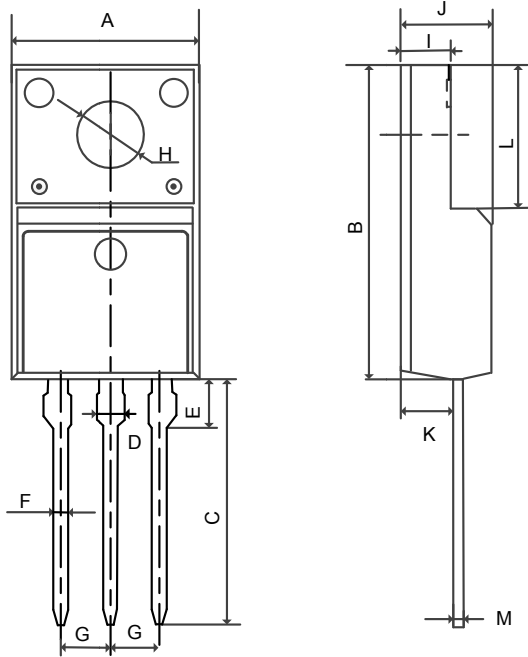


**Unclamped Inductive Switching Test Circuit & Waveforms**



## Mechanical Dimensions for TO-220F

## COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.67	16.07
C	12.70	13.30
D	1.12	1.32
E	1.85	2.15
F	0.59	0.79
G	2.39	2.69
H	3.08	3.29
I	2.34	2.74
J	4.50	4.90
K	2.61	2.91
L	6.50	6.90
M	0.40	0.60

## Mechanical Dimensions for TO-263

## COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.49	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.45	8.90
D4	6.60	—
E	9.86	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.70
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°



## Mechanical Dimensions for TO-262

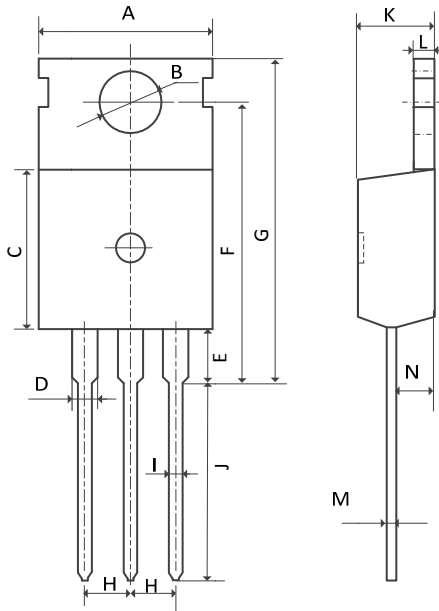
## COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.49	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.53
D	23.20	24.02
D1	8.45	8.90
D2	6.00	—
E1	9.86	10.40
E4	7.06	—
e	2.54BSC	
G	1.25	1.50
H2	—	1.50
L	13.33	14.16
L1	3.50	4.00
L3	1.28	1.58

## Mechanical Dimensions for TO-220

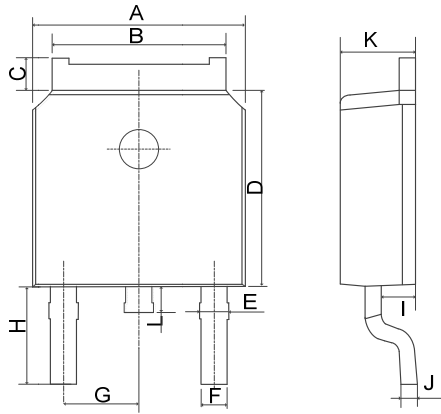
## COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Mechanical Dimensions for TO-252

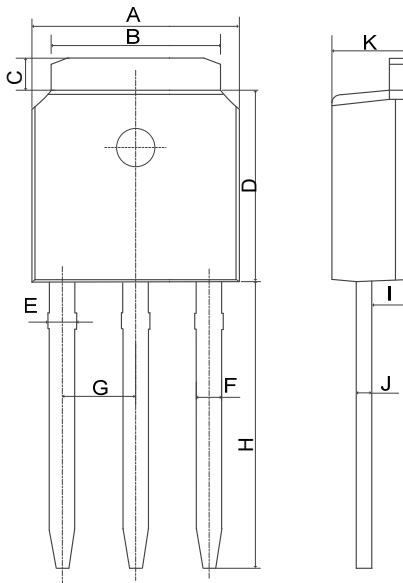
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

## Mechanical Dimensions for TO-251

## COMMON DIMENSIONS

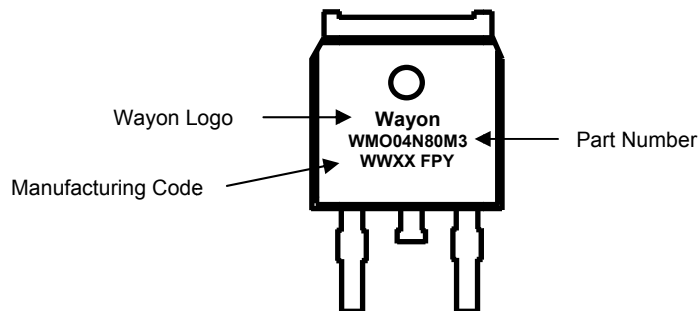


SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	9.00	9.65
I	0.85	1.17
J	0.40	0.61
K	2.10	2.50

## Ordering Information

Part	Package	Marking	Packing method
WML04N80M3	TO-220F	WML04N80M3	Tube
WMM04N80M3	TO-263	WMM04N80M3	Tape and Reel
WMO04N80M3	TO-252	WMO04N80M3	Tape and Reel
WMP04N80M3	TO-251	WMP04N80M3	Tube
WMK04N80M3	TO-220	WMK04N80M3	Tube
WMN04N80M3	TO-262	WMN04N80M3	Tube

## Marking Information



## Contact Information

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